

Data Sheet January 2000 File Number 3397.3

## 30A, 1200V Ultrafast Diode

The RURP30120 is an ultrafast diode with soft recovery characteristic ( $t_{rr}$  < 110ns). It has low forward voltage drop and is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as a freewheeling/clamping diode and rectifier in a variety of switching power supplies and other power switching applications. Its low stored charge and ultrafast recovery with soft recovery characteristic minimize ringing and electrical noise in many power switching circuits, reducing power loss in the switching transistors.

Formerly developmental type TA49031.

## **Ordering Information**

| PART NUMBER | PACKAGE  | BRAND    |  |  |
|-------------|----------|----------|--|--|
| RURP30120   | TO-220AC | RUR30120 |  |  |

NOTE: When ordering, use the entire part number.

# Symbol



#### **Features**

|   | Ultrafast with Soft Recovery |        |
|---|------------------------------|--------|
| • | Operating Temperature        | .175°C |
| ٠ | Reverse Voltage              | .1200V |

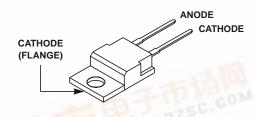
- Avalanche Energy Rated
- · Planar Construction

## **Applications**

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

# **Packaging**

JEDEC TO-220AC



# **Absolute Maximum Ratings** T<sub>C</sub> = 25°C, Unless Otherwise Specified

|   | RURP30120  | UNITS |
|---|------------|-------|
| Peak Repetitive Reverse VoltageV <sub>RRM</sub> | 1200       | V     |
| Working Peak Reverse Voltage                    | 1200       | V     |
| DC Blocking Voltage                             | 1200       | V     |
| Average Rectified Forward Current               | 30         | Α     |
| Repetitive Peak Surge Current                   | 60         | Α     |
| Nonrepetitive Peak Surge Current                | 300        | Α     |
| Maximum Power Dissipation                       | 125        | W     |
| Avalanche Energy (See Figures 7 and 8)          | 30         | mJ    |
| Operating and Storage Temperature               | -65 to 175 | οС    |



 $\textbf{Electrical Specifications} \hspace{0.5cm} \textbf{T}_{C} = 25^{o}\text{C}, \hspace{0.1cm} \textbf{Unless Otherwise Specified}$ 

| SYMBOL          | TEST CONDITION                                     | MIN | TYP | MAX | UNITS |
|-----------------|--|-----|-----|-----|-------|
| V <sub>F</sub>  | I <sub>F</sub> = 30A                               | -   | -   | 2.1 | V     |
|                 | $I_F = 30A$ , $T_C = 150^{\circ}C$                 | -   | -   | 1.9 | V     |
| I <sub>R</sub>  | V <sub>R</sub> = 1200V                             | -   | -   | 250 | μΑ    |
|                 | $V_R = 1200V, T_C = 150^{\circ}C$                  | -   | -   | 1   | mA    |
| t <sub>rr</sub> | I <sub>F</sub> = 1A, dI <sub>F</sub> /dt = 100A/μs | -   | -   | 110 | ns    |
|                 | $I_F = 30A$ , $dI_F/dt = 100A/\mu s$               | -   | -   | 150 | ns    |
| ta              | $I_F = 30A$ , $dI_F/dt = 100A/\mu s$               | -   | 90  | -   | ns    |
| t <sub>b</sub>  | $I_F = 30A$ , $dI_F/dt = 100A/\mu s$               | -   | 45  | -   | ns    |
| $R_{	heta JC}$  |  | -   | -   | 1.2 | °C/W  |

#### **DEFINITIONS**

 $V_F$  = Instantaneous forward voltage (pw = 300 $\mu$ s, D = 2%).

 $I_R$  = Instantaneous reverse current.

t<sub>rr</sub> = Reverse recovery time (See Figure 6), summation of t<sub>a</sub> + t<sub>b</sub>.

t<sub>a</sub> = Time to reach peak reverse current (See Figure 6).

 $t_b$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 6).

 $R_{\theta JC}$  = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

# **Typical Performance Curves**

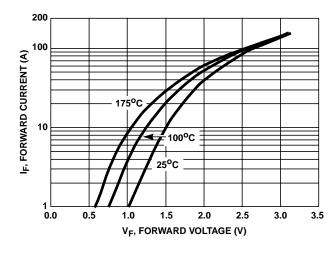


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

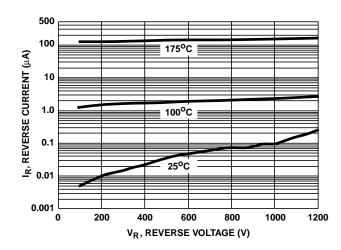


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

---

## Typical Performance Curves (Continued)

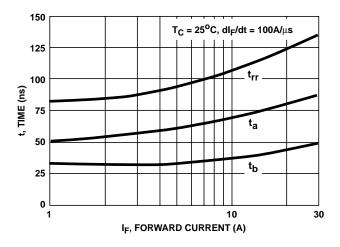


FIGURE 3. t<sub>rr</sub>, t<sub>a</sub> AND t<sub>b</sub> CURVES vs FORWARD CURRENT

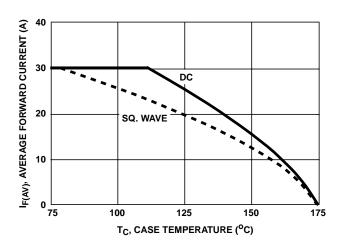


FIGURE 4. CURRENT DERATING CURVE

#### Test Circuits and Waveforms

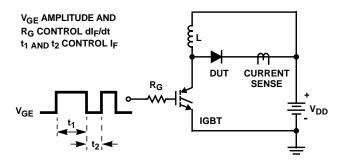


FIGURE 5. t<sub>rr</sub> TEST CIRCUIT

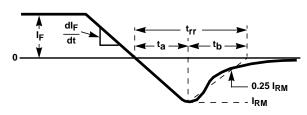


FIGURE 6. t<sub>rr</sub> WAVEFORMS AND DEFINITIONS

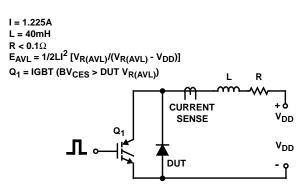


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

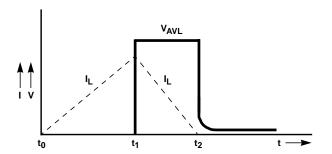


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com